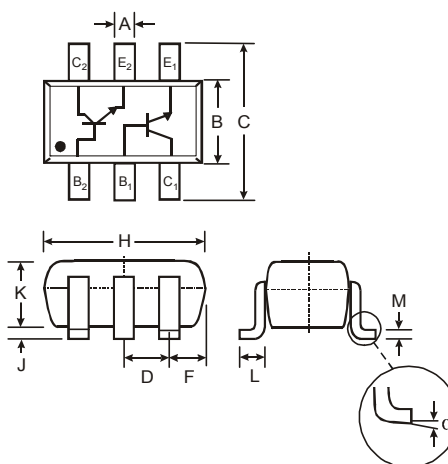


Features

- Epitaxial Planar Die Construction
- Intrinsically Matched NPN Pair (Note 1)
- Small Surface Mount Package
- 2% Matched Tolerance, h_{FE} , $V_{CE(SAT)}$, $V_{BE(SAT)}$
- **Lead Free/RoHS Compliant (Note 3)**
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.015 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

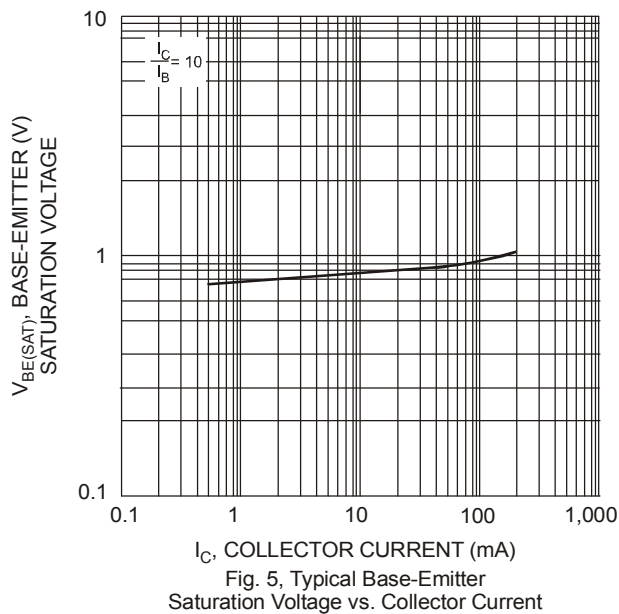
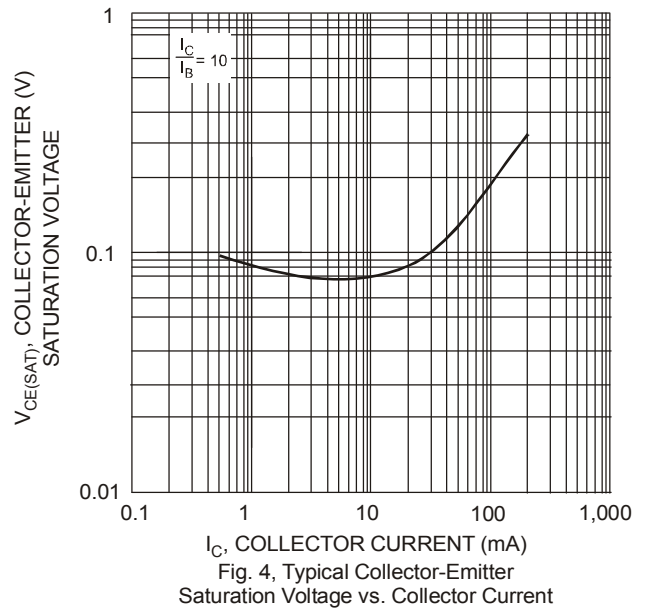
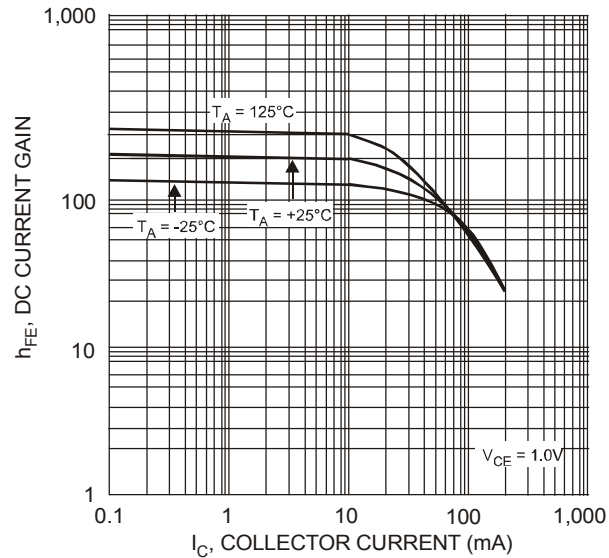
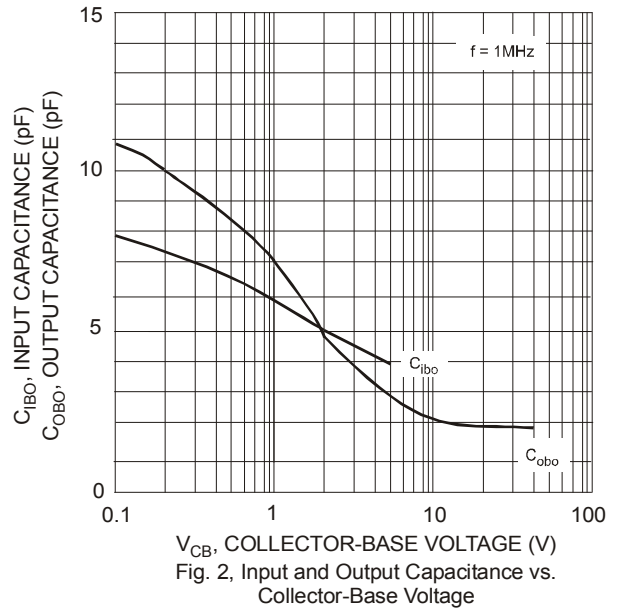
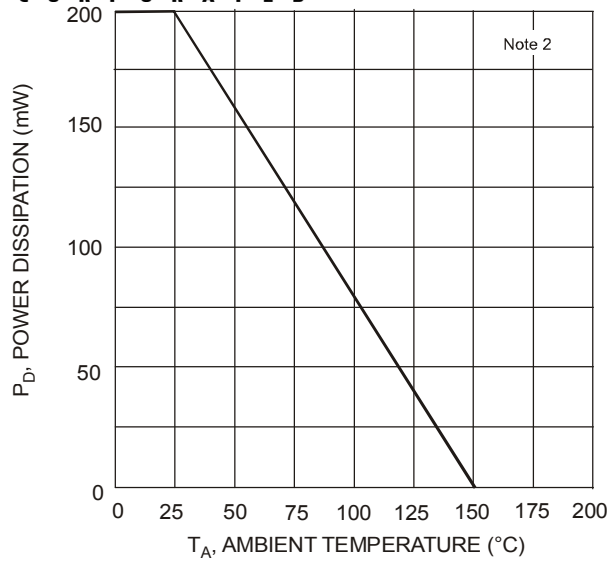
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	200	mA
Power Dissipation (Note 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Built with adjacent die from a single wafer.
 2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. No purposefully added lead.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 6)					
DC Current Gain (Note 7)	h _{FE}	40 70 100 60 30	— — 300 — —	—	I _C = 100μA, V _{CE} = 1.0V I _C = 1.0mA, V _{CE} = 1.0V I _C = 10mA, V _{CE} = 1.0V I _C = 50mA, V _{CE} = 1.0V I _C = 100mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage (Note 7)	V _{CE(SAT)}	—	0.20 0.30	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage (Note 7)	V _{BE(SAT)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Voltage Matching	ΔV _{BE}	—	1	mV	V _{CE} = 5V, I _C = 2mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.0	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	8.0	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.0	10	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.5	8	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz
Noise Figure	NF	—	5.0	dB	V _{CE} = 5.0V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = 3.0V, I _C = 10mA, V _{BE(off)} = -0.5V, I _{B1} = 1.0mA
Rise Time	t _r	—	35	ns	
Storage Time	t _s	—	200	ns	V _{CC} = 3.0V, I _C = 10mA,
Fall Time	t _f	—	50	ns	I _{B1} = I _{B2} = 1.0mA

- Notes:
6. Short duration pulse test used to minimize self-heating effect.
 7. The DC current gain, h_{FE}, (matched at I_C = 10mA and V_{CE} = 1.0V) Collector Emitter Saturation Voltage, V_{CE(SAT)}, and Base Emitter Saturation Voltage, V_{BE(SAT)} are matched with typical matched tolerances of 1% and maximum of 2%.

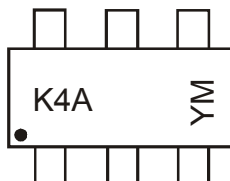


Ordering Information (Note 8)

Device	Packaging	Shipping
DMMT3904W-7-F	SOT-363	3000/Tape & Reel

Notes: 8. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K4A = Product Type Marking Code

YM = Date Code Marking

Y = Year ex: T = 2006

M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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